



5 V Fast Infrared Transceiver Module Family (FIR, 4 Mbit/s)



Description

The TFDU6100, TFDS6500, and TFDT6500 are a family of low-power infrared transceiver modules compliant to the IrDA 1.2 standard for fast infrared (FIR) data communication, supporting IrDA speeds up to 4.0 Mbit/s, HP-SIR, Sharp ASK and carrier based remote control modes up to 2 MHz. Integrated within the transceiver modules are a photo PIN diode, infrared emitter (IRED), and a low-power CMOS control IC to provide a total front-end solution in a single package. Vishay Telefunken's FIR transceivers are available in three package options, including our Baby Face package (TFDU6100), the smallest FIR

transceiver available on the market. This wide selection provides flexibility for a variety of applications and space constraints. The transceivers are capable of directly interfacing with a wide variety of I/O chips which perform the modulation/ demodulation function, including National Semiconductor's PC87338, PC87108 and PC87109, SMC's FDC37C669, FDC37N769 and CAM35C44, and Hitachi's SH3. At a minimum, a current-limiting resistor in series with the infrared emitter and a V_{CC} bypass capacitor are the only external components required to implement a complete solution.

Features

- Compliant to IrDA 1.2 (Up to 4 Mbit/s), HP-SIR[®], Sharp ASK[®] and TV Remote
- For 4.5 V to 5.5 V Operating Voltage
- Low-Power Consumption (5 mA Supply Current)
- Power Shutdown Mode (35 μ A Shutdown Current)
- Three Surface Mount Package Options
 - Universal (9.7 \times 4.7 \times 4.0 mm)
 - Side View (13.0 \times 5.95 \times 5.3 mm)
 - Top View (13.0 \times 7.6 \times 5.95 mm)
- Baby Face (Universal) Package Capable of Surface Mount Solderability to Side and Top View Orientation
- Directly Interfaces with Various Super I/O and Controller Devices
- Built-In EMI Protection – No External Shielding Necessary
- Few External Components Required
- Backward Compatible to all Telefunken SIR and FIR Infrared Transceivers

Applications

- Notebook Computers, Desktop PCs, Palmtop Computers (Win CE, Palm PC), PDAs
- Digital Still and Video Cameras
- Printers, Fax Machines, Photocopiers, Screen Projectors
- Telecommunication Products (Cellular Phones, Pagers)
- Internet TV Boxes, Video Conferencing Systems
- External Infrared Adapters (Dongles)
- Medical and Industrial Data Collection Devices

Package Options

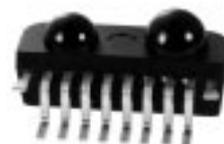
TFDU6100
Baby Face (Universal)



TFDS6500
Side View



TFDT6500
Top View



Ordering Information

| Part Number | Qty / Reel | Description |
|--------------|------------|---|
| TFDU6100-TR3 | 1000 pcs | Oriented in carrier tape for side view surface mounting |
| TFDU6100-TT3 | 1000 pcs | Oriented in carrier tape for top view surface mounting |
| TFDS6500-TR3 | 750 pcs | |
| TFDT6500-TR3 | 750 pcs | |

Functional Block Diagram

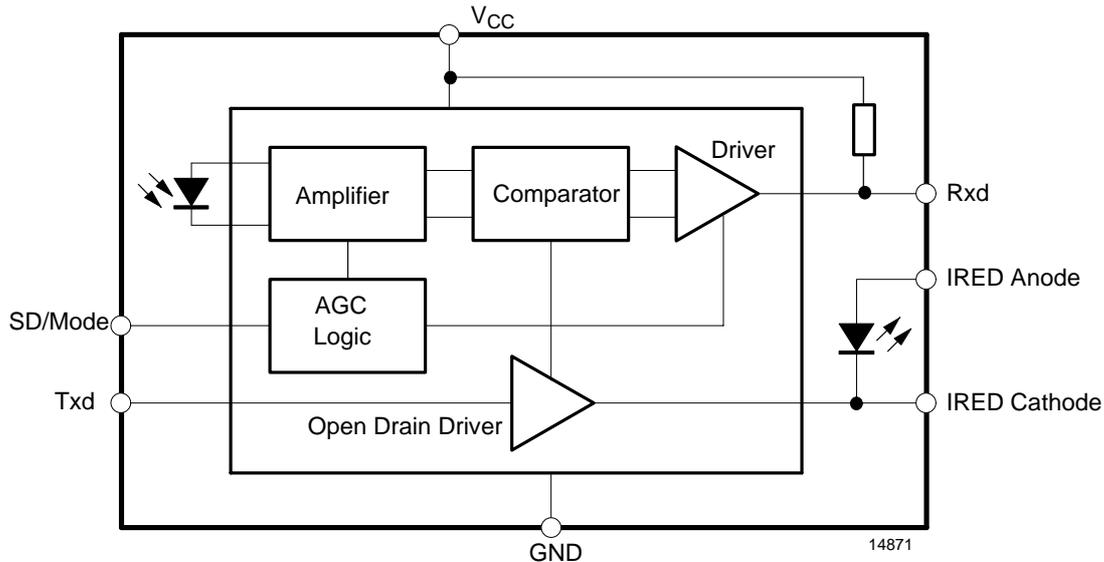


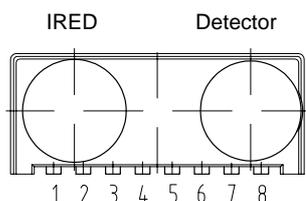
Figure 1. Functional Block Diagram

Pin Description

| Pin Number | | Function | Description | I/O | Active |
|--------------------|------------|--------------|---|-----|--------|
| "U" and "T" Option | "S" Option | | | | |
| 1 | 8 | IRED Anode | IRED anode, to be externally connected to V_{CC} through a current control resistor | | |
| 2 | 1 | IRED Cathode | IRED cathode, internally connected to driver transistor | | |
| 3 | 7 | Txd | Transmit Data Input | I | HIGH |
| 4 | 2 | Rxd | Received Data Output, push-pull CMOS driver output capable of driving a standard CMOS or TTL load. No external pull-up or pull-down resistor is required (pin is floating when device is in shut-down mode) | O | LOW |
| 5 | 6 | SD/Mode | Shutdown/Mode | I | HIGH |
| 6 | 3 | V_{CC} | Supply Voltage | | |
| 7 | 5 | NC | Do not connect | | |
| 8 | 4 | GND | Ground | | |

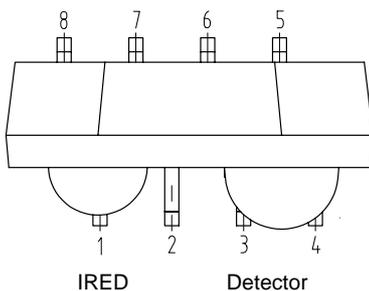


“U” Option Baby Face (Universal)



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“S” Option Side View



“T” Option Top View

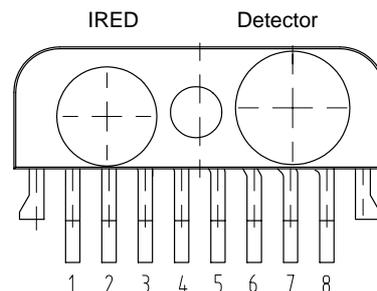


Figure 2. Pinnings

Absolute Maximum Ratings

Reference point Pin GND unless otherwise noted.

Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

| Parameters | Test Conditions | Symbol | Min. | Typ. | Max. | Unit |
|--|---|-----------------|------|------|--------------|-------|
| Supply Voltage Range | | V_{CC} | -0.5 | | 6 | V |
| Power Dissipation | See Derating Curve | P_D | | | 350 | mW |
| Junction Temperature | | T_J | | | 125 | °C |
| Ambient Temperature Range (Operating) | | T_{amb} | -25 | | +85 | °C |
| Storage Temperature Range | | T_{stg} | -25 | | +85 | °C |
| Soldering Temperature | See Recommended Solder Profile (see figure 9) | | | | 240 | °C |
| Average Output Current | | $I_{IRED (DC)}$ | | | 130 | mA |
| Repetitive Pulsed Output Current | $<90 \mu s, t_{on} <20\%$ | $I_{IRED (RP)}$ | | | 600 | mA |
| IRED Anode Voltage | | $V_{IRED A}$ | -0.5 | | $V_{CC}+0.5$ | V |
| Transmitter Data Input Voltage | | V_{Txd} | -0.5 | | $V_{CC}+0.5$ | V |
| Receiver Data Output Voltage | | V_{Rxd} | -0.5 | | $V_{CC}+0.5$ | V |
| Virtual Source Size | Method: (1-1/e) encircled energy | d | 2.5 | 2.8 | | mm |
| Maximum Intensity for Class 1 Operation of IEC825-1 or EN60825-1 (worst case IrDA FIR pulse pattern) | EN60825, 1997 | | | | 320 | mW/sr |

Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, $V_{CC} = 5.0\text{ V}$ unless otherwise noted.

Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

| Parameters | Test Conditions / Pins | Symbol | Min. | Typ. | Max. | Unit |
|---------------------------------|---|----------|----------------|------|------|--------------------|
| Transceiver | | | | | | |
| Supply Voltage | | V_{CC} | 4.5 | 5 | 5.5 | V |
| Dynamic Supply Current | SD = Low Receive mode only. In transmit mode, add additional 100 mA (typ) for IRED current. | I_{CC} | | 5 | 7 | mA |
| Standby Supply Current | SD = $V_{CC} - 0.5$ | I_{SD} | | 35 | 100 | μA |
| Operating Temperature Range | | T_A | -25 | | +85 | $^{\circ}\text{C}$ |
| Output Voltage Low | $I_{OL} = 2.5\text{ mA}$ | V_{OL} | | 0.3 | 0.5 | V |
| Output Voltage High | $I_{OH} = -2.5\text{ mA}$ | V_{OH} | $V_{CC} - 0.5$ | | | V |
| Input Voltage Low (T_{xd}) | | V_{IL} | 0 | | 0.8 | V |
| Input Voltage High (T_{xd}) | | V_{IH} | 3.5 | | | V |
| Input Voltage Low (SD/Mode) | | V_{IL} | 0 | | 0.8 | V |
| Input Voltage High (SD/Mode) | | V_{IH} | $V_{CC} - 0.5$ | | | V |
| Input Leakage Current | | I_L | -10 | | +10 | μA |
| Input Capacitance | | C_I | | | 5 | pF |



Optoelectronic Characteristics

$T_{amb} = 25^{\circ}\text{C}$, $V_{CC} = 5.0\text{ V}$ unless otherwise noted.

Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

| Parameters | Test Conditions | Symbol | Min. | Typ. | Max. | Unit |
|---|---|----------------------------|------|----------|------|------------------------|
| Receiver | | | | | | |
| Minimum Detection Threshold Irradiance | 9.6 kbit/s to 115.2 kbit/s, $\lambda = 850\text{ nm} - 900\text{ nm}$ | E_e | | 25 | 35 | mW/m^2 |
| | 1.152 Mbit/s to 4 Mbit/s, $\lambda = 850\text{ nm} - 900\text{ nm}$ | E_e | | 70 | 80 | mW/m^2 |
| Maximum Detection Threshold Irradiance | | E_e | 5 | 10 | | kW/m^2 |
| Logic LOW Receiver Input Irradiance | | E_e | 4 | | | mW/m^2 |
| Rise Time of Output Signal | 10% to 90%, @2.2 k Ω , 15pF | $t_r(\text{Rxd})$ | 10 | | 40 | ns |
| Fall Time of Output Signal | 90% to 10%, @2.2 k Ω , 15pF | $t_f(\text{Rxd})$ | 10 | | 40 | ns |
| Rxd Pulse Width of Output Signal, 50% | Input pulse length 20 μs , 9.6 kbit/s | t_{PW} | 0.8 | | 20 | μs |
| | Input pulse length 125 ns, 4.0 Mbit/s mode | t_{PW} | 60 | | 165 | ns |
| | Input pulse length 250 ns, 4.0 Mbit/s mode (double pulse) | t_{PW} | 185 | | 290 | ns |
| Jitter, Leading Edge | Input Irradiance = 90 mW/m^2 , 4.0 Mbit/s mode | | | | 10 | ns |
| Latency | | t_L | | | 120 | μs |
| Transmitter | | | | | | |
| IRED Operating Current | $R1 = 7.2\ \Omega$, $V_{CC} = 5.0\text{ V}$ | I_D | | 0.4 | 0.55 | A |
| Output Radiant Intensity | $V_{CC} = 5.0\text{ V}$, $\alpha = 0^{\circ}$, 15° Txd = Low or SD = High (Receiver is inactive as long as SD = High) $R1 = 7.2\ \Omega$ | I_e | | | 0.04 | mW/sr |
| | $V_{CC} = 5.0\text{ V}$, $\alpha = 0^{\circ}$, 15° Txd = High, SD = Low, $R1 = 7.2\ \Omega$ | I_e | 100 | 140 | 320 | mW/sr |
| Radiant Intensity, Half – Intensity Angle | | $\alpha_{1/2}$ | | ± 24 | | $^{\circ}$ |
| Peak – Emission Wavelength | | λ_p | 880 | | 900 | nm |
| Optical Rise Time, Fall Time | | t_{ropt} , t_{fopt} | 10 | | 40 | ns |
| Optical Overshoot | | | | | 25 | % |

Recommended Circuit Diagram

The only required component for designing an IrDA 1.2 compatible design using Telefunken FIR transceivers is a current limiting resistor, R1, to the IRED. However, depending on the entire system design and board layout, additional components may be required (see figure 3).

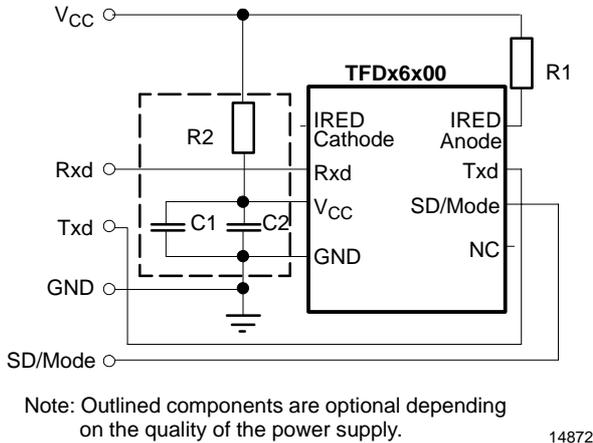


Figure 3. Recommended Application Circuit

Telefunken FIR transceivers integrate a sensitive receiver and a built-in power driver. The combination of both needs a careful circuit board layout. The use of thin, long resistive and inductive wiring should be avoided. The inputs (Txd, SD/Mode) and the output Rxd should be directly (DC) coupled to the I/O circuit.

R1 is used for controlling the current through the IR emitter. For increasing the output power of the IRED, the value of the resistor should be reduced. Similarly, to reduce the output power of the IRED, the value of the resistor should be increased. For typical values of R1 see figure 4. For IrDA compliant operation, a

current control resistor of 7.2 Ω is recommended. The upper drive current limitation is dependent on the duty cycle and is given by the absolute maximum ratings on the data sheet.

R2, C1 and C2 are optional and dependent on the quality of the supply voltage V_{CC} and injected noise. An unstable power supply with dropping voltage during transmission may reduce sensitivity (and transmission range) of the transceiver.

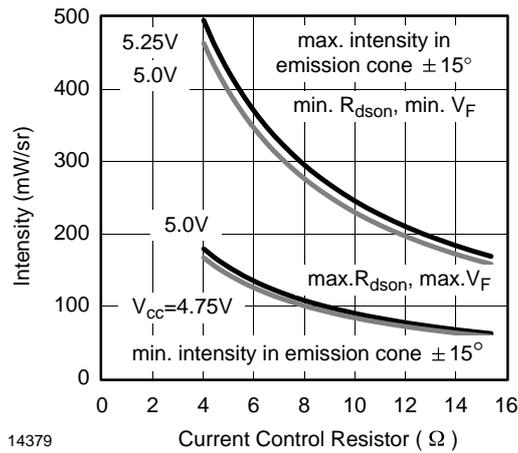


Figure 4. Intensity I_e vs. Current Control Resistor R1

The placement of these parts is critical. It is strongly recommended to position C2 as near as possible to the transceiver power supply pins. A tantalum capacitor should be used for C1 while a ceramic capacitor is used for C2. Also, when connecting the described circuit to the power supply, low impedance wiring should be used.

Table 1. Recommended Application Circuit Components

| Component | Recommended Value | Vishay Part Number |
|-----------|---|----------------------|
| C1 | 4.7 μF, Tantalum | 293D 475X9 016B 2T |
| C2 | 0.1 μF, Ceramic | VJ 1206 Y 104 J XXMT |
| R1 | 7.2 Ω , 0.25 W (recommend using two 3.6 Ω, 0.125 W resistors in series) | CRCW-1206-3R60-F-RT2 |
| R2 | 47 Ω , 0.125 W | CRCW-1206-47R0-F-RT2 |

Mode Switching

The TFDU6100, TFDS6500 and TFDT6500 powers on with a default of low frequency mode.

The low frequency mode covers speeds up to 115.2 kbit/s. Signals with higher data rates should be detected in the high frequency mode. Lower-frequency data can also be received in the high frequency mode but with reduced sensitivity. To switch the transceivers from low frequency mode to the 4.0 Mbit/s mode and vice versa, the programming sequences described below are required.

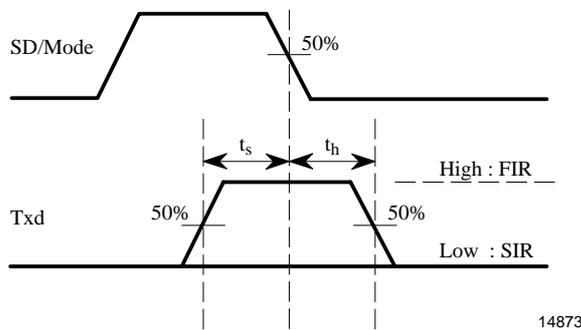


Figure 5. Mode Switching Timing Diagram

Setting to the High Bandwidth Mode (0.576 Mbit/s to 4.0 Mbit/s)

1. Set SD/MODE input to logic "HIGH".
2. Set Txd input to logic "HIGH". Wait $t_s \geq 200$ ns.
3. Set SD/MODE to logic "LOW" (this negative edge latches state of Txd, which determines speed setting).
4. After waiting $t_h \geq 200$ ns Txd can be set to logic "LOW". The hold time of Txd is limited by the maximum allowed pulse length.

Txd is now enabled as normal Txd input for the high bandwidth mode.

Setting to the Lower Bandwidth Mode (2.4 kbit/s to 115.2 kbit/s)

1. Set SD/MODE input to logic "HIGH".
2. Set Txd input to logic "LOW". Wait $t_s \geq 200$ ns.
3. Set SD/MODE to logic "LOW" (this negative edge latches state of Txd, which determines speed setting).
4. Txd must be held for $t_h \geq 200$ ns.

Txd is now enabled as normal Txd input for the lower bandwidth mode.

Recommended SMD Pad Layout

The leads of the device should be soldered in the center position of the pads.

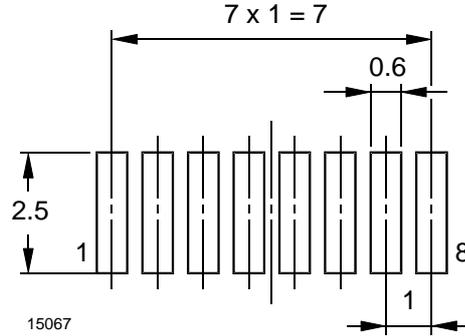


Figure 6. TFDU6100 BabyFace (Universal)

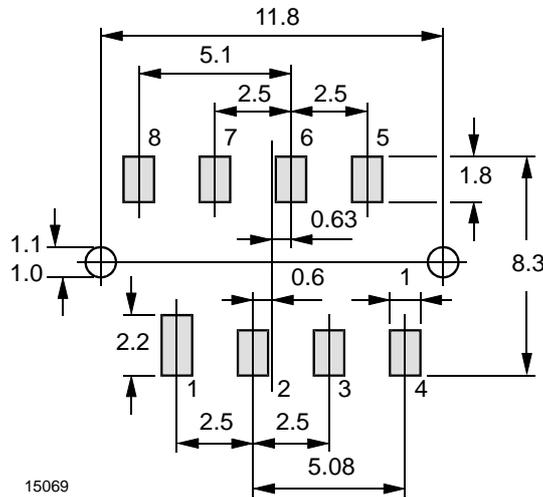


Figure 7. TFDS6500 Side View Package

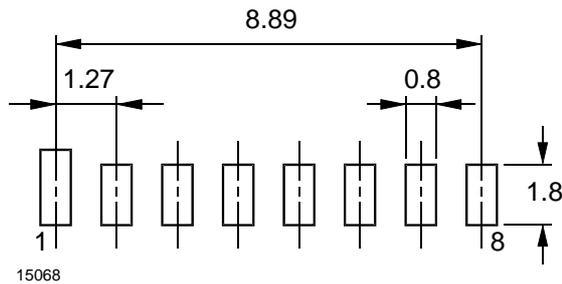


Figure 8. TFDT6500 Top View Package

Note: Leads of the device should be at least 0.3 mm within the ends of the pads.
Pad 1 is longer to designate Pin 1 connection to transceiver.



Recommended Solder Profile

Current Derating Diagram

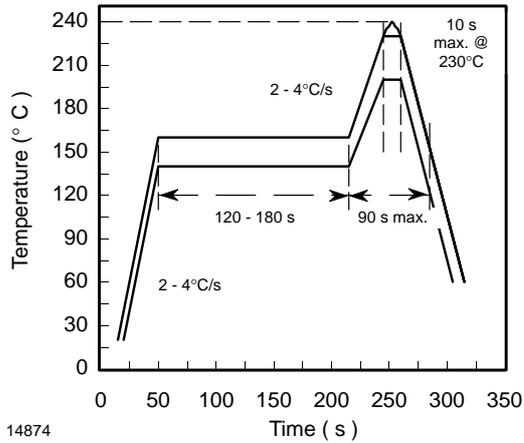


Figure 9. Recommended Solder Profile

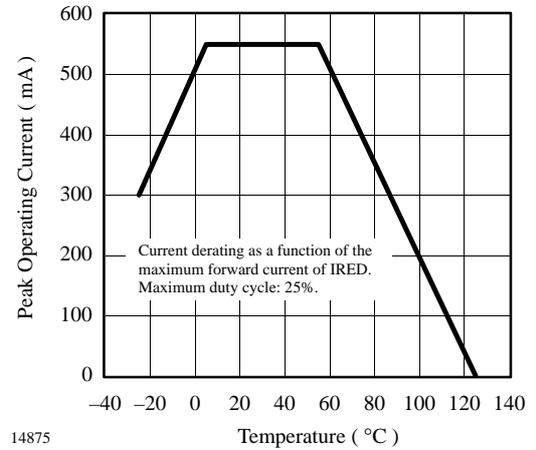
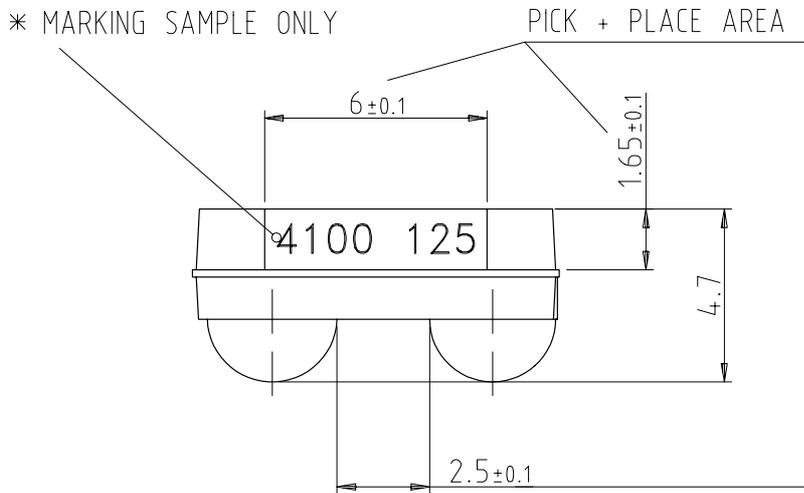
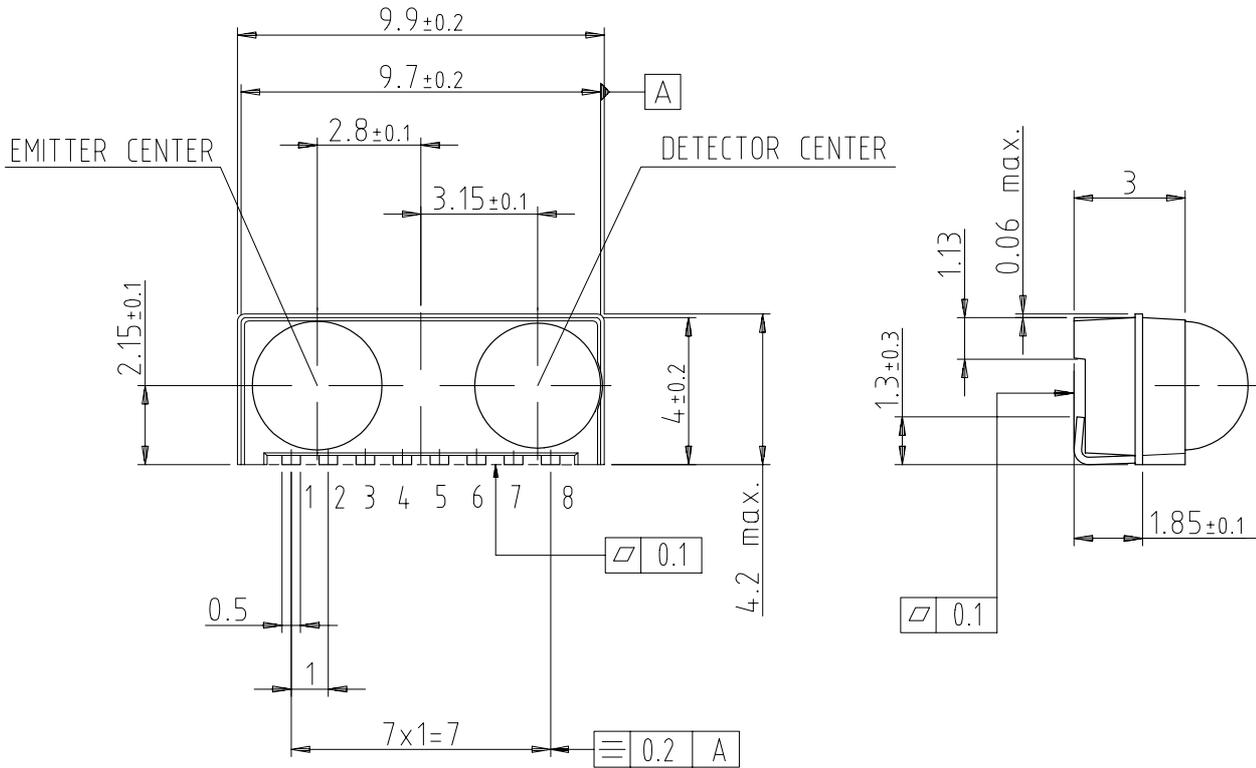


Figure 10. Current Derating Diagram

TFDU6100 – Baby Face (Universal) Package (Mechanical Dimensions)



* MARKING ORIENTATION
180 DEGREES ALLOWED

Drawing-No.: 6.550-5148.01-4
Issue: 8; 10.7.98

12249

 technical drawings
 according to DIN
 specifications



Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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